



2N6107
2N6111

SILICON PNP SWITCHING TRANSISTORS

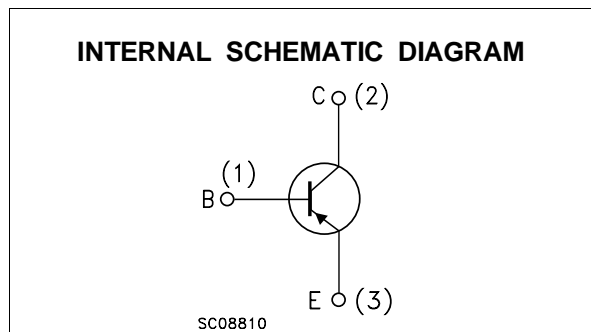
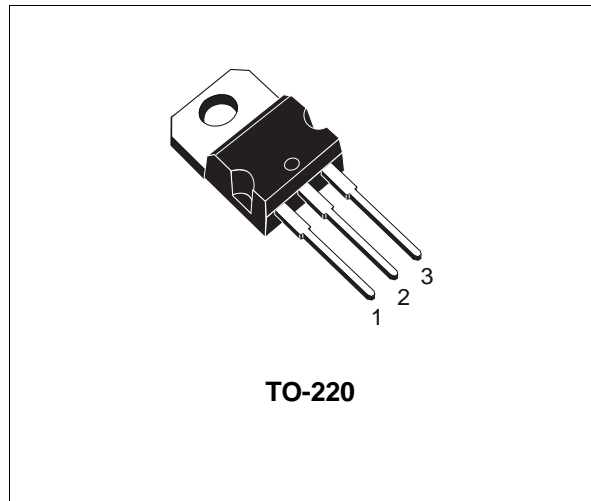
- STMicroelectronics PREFERRED SALESTYPE
- PNP TRANSISTORS

APPLICATIONS:

- LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

DESCRIPTION

The 2N6107 and 2N6111 are epitaxial-base PNP silicon transistors in Jedec TO-220 plastic package. They are intended for a wide variety of medium power switching and linear applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		2N6107	2N6111	
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	80	40	V
V_{CEX}	Collector-Emitter Voltage ($R_{BE} = 100 \Omega$)	80	40	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	70	30	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	5		V
I_C	Collector Current	7		A
I_B	Base Current	3		A
P_{tot}	Total Dissipation at $T_c = 25^\circ\text{C}$	40		W
T_{stg}	Storage Temperature	-65 to 150		$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	150		$^\circ\text{C}$

For PNP devices voltage and current values are negative

2N6107/2N6111

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	3.12	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	70	°C/W

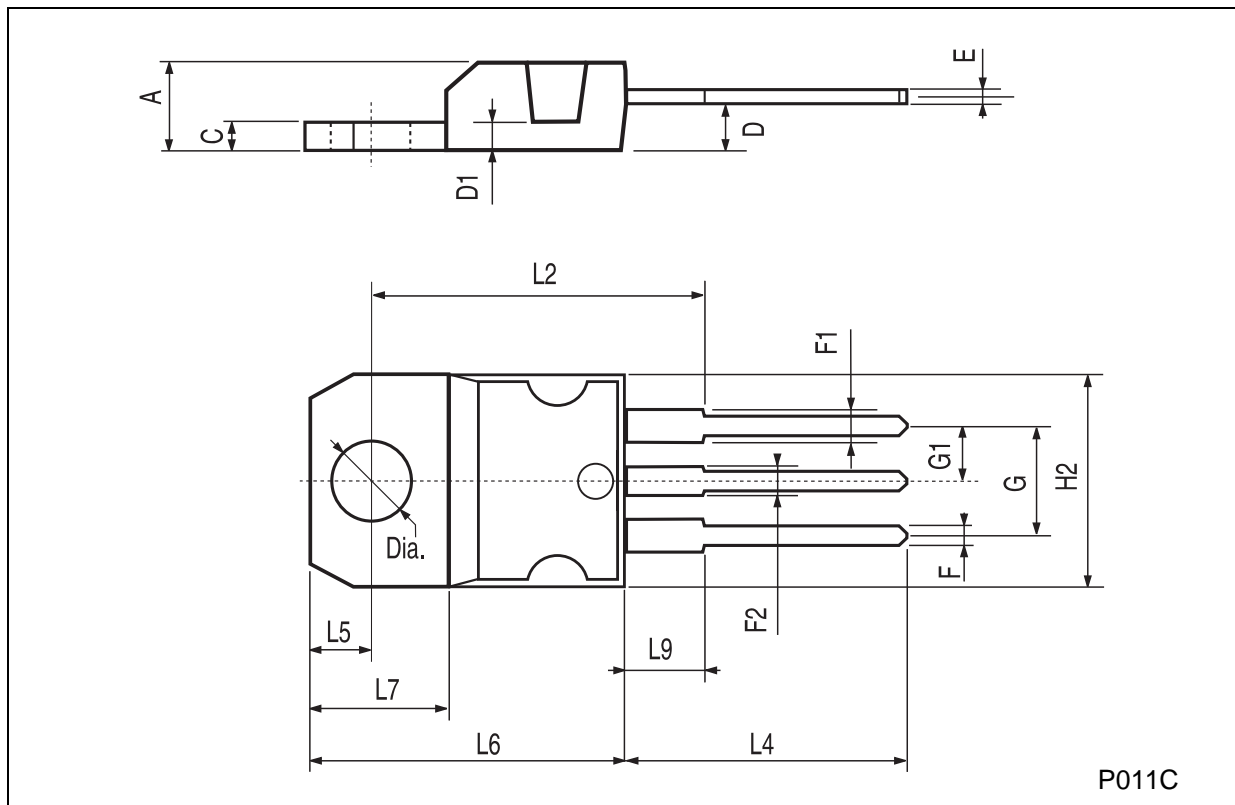
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CEX}	Collector Cut-off Current (V _{BE} = - 1.5V)	for 2N6107 V _{CE} = 80 V			0.1	mA
		for 2N6111 V _{CE} = 40 V			0.1	mA
		for 2N6107 V _{CE} = 70 V			2	mA
		for 2N6111 V _{CE} = 30 V			2	mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	for 2N6107 V _{CE} = 60 V			1	mA
		for 2N6111 V _{CE} = 20 V			1	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)*}	Collector-emitter Sustaining Voltage	I _C = 0.1 A for 2N6107 for 2N6111	70			V
			30			V
V _{CER(sus)*}	Collector-emitter Sustaining Voltage (I _C = 0)	I _C = 0.1 A R _{BE} = 100 Ω for 2N6107 for 2N6111	80			V
			40			V
V _{CE(sat)*}	Collector-emitter Saturation Voltage	I _C = 3 A I _B = 0.3 A for 2N6107			1	V
		I _C = 2 A I _B = 0.2 A for 2N6111			1	V
		I _C = 7 A I _B = 3.0 A			3.5	V
V _{BE(on)*}	Base-emitter Voltage	I _C = 3 A V _{CE} = 4 V for 2N6107			1.5	V
		I _C = 2 A V _{CE} = 4 V for 2N6111			1.5	V
		I _C = 7 A V _{CE} = 4 V			3	V
h _{FE} *	DC Current Gain	I _C = 2 A V _{CE} = 4 V for 2N6107	30		150	
		I _C = 3 A V _{CE} = 4 V for 2N6111	30		150	
		I _C = 7 A V _{CE} = 4 V	2.3			
h _{fe}	Small Signal Current Gain	I _C = 0.5 A V _{CE} = 4 V f = 50 KHz	20			
f _T	Transition-Frequency	I _C = 0.5 A V _{CE} = 4 V	4			MHz
C _{cbo}	Collector-base Capacitance	V _{CB} = 10 V f = 1 MHz			250	pF

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %.
For PNP types voltage and current values are negative.
For characteristic curves see the bd534 (PNP) series.

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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